

Takashi Sekiguchi

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5920534/publications.pdf>

Version: 2024-02-01

451
papers

13,470
citations

30551

56
h-index

37326

100
g-index

464
all docs

464
docs citations

464
times ranked

13238
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomic-scale investigation of implanted Mg in GaN through ultra-high-pressure annealing. Journal of Applied Physics, 2022, 131, .	1.1	8
2	Stable single atomic silver wires assembling into a circuitry-connectable nanoarray. Nature Communications, 2021, 12, 1191.	5.8	19
3	Cathodoluminescence Investigation of Stacking Faults and Dislocations in the Edge Part of Seed-Grown $\langle 110 \rangle$ -Plane GaN Substrate. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100175.	0.8	3
4	Composition dependent properties of p- and n-type polycrystalline group-IV alloy thin films. Journal of Alloys and Compounds, 2021, 887, 161306.	2.8	5
5	Electron-Beam-Induced Current and Cathodoluminescence Study of Dislocations in SrTiO ₃ . Crystals, 2020, 10, 736.	1.0	3
6	Influence of implanted Mg concentration on defects and Mg distribution in GaN. Journal of Applied Physics, 2020, 128, .	1.1	16
7	Mg diffusion and activation along threading dislocations in GaN. Applied Physics Letters, 2020, 116, .	1.5	12
8	Electron-Beam-Induced Current Study of Dislocations and Leakage Sites in GaN Schottky Barrier Diodes. Journal of Electronic Materials, 2020, 49, 5196-5204.	1.0	3
9	Analysis on the Shapes of the Shockley type Stacking Faults Generated by the REDG Effect in the 4H-SiC Power Devices. Nihon Kessho Gakkaishi, 2020, 62, 150-157.	0.0	0
10	Cathodoluminescence and scanning transmission electron microscopy study of InGaN/GaN quantum wells in core-shell GaN nanowires. Applied Physics Express, 2019, 12, 085003.	1.1	12
11	Oxygen vacancy migration along dislocations in SrTiO ₃ studied by cathodoluminescence. Journal Physics D: Applied Physics, 2019, 52, 475103.	1.3	12
12	Wafer-scale analysis of GaN substrate wafer by imaging cathodoluminescence. Applied Physics Express, 2019, 12, 051005.	1.1	5
13	Cathodoluminescence study of Mg implanted GaN: the impact of dislocation on Mg diffusion. Applied Physics Express, 2019, 12, 051010.	1.1	25
14	Energy and Direction Resolved Secondary Electron Imaging Using Fountain Detector. Journal of Surface Analysis (Online), 2019, 26, 148-149.	0.1	0
15	Morphology of single Shockley-type stacking faults generated by recombination enhanced dislocation glide in 4H-SiC. Philosophical Magazine, 2018, 98, 878-898.	0.7	17
16	Development of SEM/STEM-WDX for highly sensitive detection of light elements. Journal of Instrumentation, 2018, 13, P02025-P02025.	0.5	0
17	Valence band edge tail states and band gap defect levels of GaN bulk and In _x Ga _{1-x} N films detected by hard X-ray photoemission and photothermal deflection spectroscopy. Applied Physics Express, 2018, 11, 021002.	1.1	17
18	Reaction of europium-doped $\hat{\pm}$ -SiAlON phosphors with sodium borosilicate glass matrices. Journal of the European Ceramic Society, 2018, 38, 735-741.	2.8	11

#	ARTICLE	IF	CITATIONS
19	Low Energy Secondary Electron Imaging of Nanosheets Using Inverted Fountain Detector. <i>Microscopy and Microanalysis</i> , 2018, 24, 642-643.	0.2	0
20	Secondary electron spectroscopy for imaging semiconductor materials. , 2018, , .		0
21	Investigation of Si Dendrites by Electron-Beam-Induced Current. <i>Crystals</i> , 2018, 8, 317.	1.0	1
22	Development of a fountain detector for spectroscopy of secondary electrons in scanning electron microscopy. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 046701.	0.8	4
23	Collection efficiency and acceptance maps of electron detectors for understanding signal detection on modern scanning electron microscopy. <i>Microscopy (Oxford, England)</i> , 2018, 67, 18-29.	0.7	6
24	Surface defects generated by intrinsic origins on 4H-SiC epitaxial wafers observed by scanning electron microscopy. <i>Microscopy (Oxford, England)</i> , 2017, 66, 95-102.	0.7	5
25	Numerical analysis of the relation between dislocation density and residual strain in silicon ingots used in solar cells. <i>Journal of Crystal Growth</i> , 2017, 474, 130-134.	0.7	9
26	Investigation of V-shaped extended defects in a 4H-SiC epitaxial film. <i>Philosophical Magazine</i> , 2017, 97, 657-670.	0.7	5
27	Deep-level defects related to the emissive pits in thick InGaN films on GaN template and bulk substrates. <i>APL Materials</i> , 2017, 5, .	2.2	14
28	Enhanced cathodoluminescence of green In^{2+} -sialon:Eu ²⁺ phosphor by In ₂ O ₃ coating. <i>Journal of Alloys and Compounds</i> , 2017, 727, 1110-1114.	2.8	8
29	Initial leakage current paths in the vertical-type GaN-on-GaN Schottky barrier diodes. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	55
30	Development of a Fountain Detector for Spectroscopy of Secondary Electrons in SEM. <i>Microscopy and Microanalysis</i> , 2017, 23, 590-591.	0.2	1
31	Transition of Emission Colours as a Consequence of Heat-Treatment of Carbon Coated Ce ³⁺ -Doped YAG Phosphors. <i>Materials</i> , 2017, 10, 1180.	1.3	10
32	Cathodoluminescence study of killer defects in GaN wafers on sapphire substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700054.	0.8	3
33	Development of fountain detectors for spectroscopy of secondary electron in SEM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700057.	0.8	3
34	Cathodoluminescence study of pn-junctions in widegap materials using cross sectional polishing. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700096.	0.8	0
35	Temperature-dependent recombination velocity analysis on artificial small angle grain boundaries using electron beam induced current method. <i>Journal of Applied Physics</i> , 2016, 119, 065302.	1.1	1
36	Dislocation behavior in seed-cast grown Si ingots based on crystallographic orientation. <i>Progress in Photovoltaics: Research and Applications</i> , 2016, 24, 1513-1522.	4.4	10

#	ARTICLE	IF	CITATIONS
37	High homogeneity, thermal stability and external quantum efficiency of Ce:YAG single-crystal powder phosphors for white LEDs. Journal of the Ceramic Society of Japan, 2016, 124, 574-578.	0.5	5
38	Prevention of thermal- and moisture-induced degradation of the photoluminescence properties of the Sr ₂ Si ₅ N ₈ :Eu ²⁺ red phosphor by thermal post-treatment in N ₂ atmosphere. Physical Chemistry Chemical Physics, 2016, 18, 12494-12504.	1.3	36
39	Ternary In ₂ S ₃ /In ₂ O ₃ heterostructures and their cathodoluminescence. RSC Advances, 2016, 6, 51089-51095.	1.7	4
40	Investigation of dislocations in Nb-doped (100) SrTiO ₃ single crystals and their impacts on resistive switching. Superlattices and Microstructures, 2016, 99, 182-185.	1.4	5
41	Effect of 3 rd generation on random grain boundaries in multicrystalline silicon. Superlattices and Microstructures, 2016, 99, 136-139.	1.4	3
42	SEM observation of p-n junction in semiconductors using fountain secondary electron detector. Superlattices and Microstructures, 2016, 99, 165-168.	1.4	4
43	Analysis of Dislocation Structures in 4H-SiC by Synchrotron X-Ray Topography. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2016, 197, 3-17.	0.2	7
44	CaAlSi ₃ :Eu ²⁺ translucent ceramic: a promising robust and efficient red color converter for solid state laser displays and lighting. Journal of Materials Chemistry C, 2016, 4, 8197-8205.	2.7	115
45	Low-energy Cathodoluminescence for (Oxy)Nitride Phosphors. Journal of Visualized Experiments, 2016, , .	0.2	2
46	Surface defects generated by extrinsic origins on 4H-SiC epitaxial-wafers observed by scanning electron microscopy. Microscopy (Oxford, England), 2016, 66, 103-109.	0.7	4
47	Imaging and spectroscopy of secondary electrons from AlN and Si ₃ N ₄ ceramics using fountain detector. Superlattices and Microstructures, 2016, 99, 41-44.	1.4	1
48	Cathodoluminescence study on the impurity behaviors at threading dislocations in GaN. Superlattices and Microstructures, 2016, 99, 77-82.	1.4	6
49	Solubility and crystallographic facet tailoring of (GaN) _{1-x} (ZnO) _x pseudobinary solid-solution nanostructures as promising photocatalysts. Nanoscale, 2016, 8, 3694-3703.	2.8	42
50	Arbitrary cross-section SEM-cathodoluminescence imaging of growth sectors and local carrier concentrations within micro-sampled semiconductor nanorods. Nature Communications, 2016, 7, 10609.	5.8	13
51	Defects and luminescence control of AlN ceramic by Si-doping. Scripta Materialia, 2016, 110, 109-112.	2.6	12
52	Cross-sectional electric field distributions in BaSi ₂ homo and BaSi ₂ /Si hetero pn junctions. , 2015, , .		1
53	B13-O-10 Low Energy Secondary Electron Imaging for Various Semiconductors using Fountain Detector. Microscopy (Oxford, England), 2015, 64, i36.1-i36.	0.7	0
54	Single-Seed Casting Large-Size Monocrystalline Silicon for High-Efficiency and Low-Cost Solar Cells. Engineering, 2015, 1, 378-383.	3.2	7

#	ARTICLE	IF	CITATIONS
55	Defect Characterization in Silicon by Electron-Beam-Induced Current and Cathodoluminescence Techniques. Lecture Notes in Physics, 2015, , 343-373.	0.3	3
56	Influence of dislocations on indium diffusion in semi-polar InGaN/GaN heterostructures. AIP Advances, 2015, 5, .	0.6	4
57	Enhanced Light Emission due to Formation of Semi-polar InGaN/GaN Multi-quantum Wells. Nanoscale Research Letters, 2015, 10, 459.	3.1	1
58	Control of extended defects in cast multicrystalline silicon using polycrystalline template. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1099-1102.	0.8	1
59	Spontaneous Ga incorporation in ZnO nanowires epitaxially grown on GaN substrate. Physica Status Solidi - Rapid Research Letters, 2015, 9, 466-469.	1.2	5
60	Control of extended defects in cast and seed cast Si ingots for photovoltaic application. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1094-1098.	0.8	0
61	Cathodoluminescence study of optical properties along the growth direction of ZnO films on GaN substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1129-1131.	0.8	1
62	Now, Scanning Electron Microscope is Attracting Much Attention of Researchers. Hyomen Kagaku, 2015, 36, 157-157.	0.0	0
63	Moisture-induced degradation and its mechanism of (Sr,Ca)AlSiN ₃ :Eu ²⁺ , a red-color-converter for solid state lighting. Journal of Materials Chemistry C, 2015, 3, 3181-3188.	2.7	75
64	Strong Energy-Transfer-Induced Enhancement of Luminescence Efficiency of Eu ²⁺ - and Mn ²⁺ -Codoped Gamma-AlON for Near-UV-LED-Pumped Solid State Lighting. Inorganic Chemistry, 2015, 54, 5556-5565.	1.9	51
65	Advantage in solar cell efficiency of high-quality seed cast mono Si ingot. Applied Physics Express, 2015, 8, 062301.	1.1	17
66	Helical Growth of Aluminum Nitride: New Insights into Its Growth Habit from Nanostructures to Single Crystals. Scientific Reports, 2015, 5, 10087.	1.6	18
67	Orientation Dependency of Dislocation Generation in Si Growth Process. Solid State Phenomena, 2015, 242, 15-20.	0.3	1
68	Threading dislocation reduction in a GaN film with a buffer layer grown at an intermediate temperature. Journal of the Korean Physical Society, 2015, 66, 214-218.	0.3	0
69	Characterization of comet-shaped defects on C-face 4H-SiC epitaxial wafers by electron microscopy. Journal of Crystal Growth, 2015, 416, 142-147.	0.7	14
70	Band-Gap Deformation Potential and Elasticity Limit of Semiconductor Free-Standing Nanorods Characterized <i>in Situ</i> by Scanning Electron Microscope and Cathodoluminescence Nanospectroscopy. ACS Nano, 2015, 9, 2989-3001.	7.3	22
71	Microanalysis of Calcium Codoped LaAl(Si ₆ Al)(N ₁₀ O) _(z-1) : Ce ³⁺ Blue Phosphor. Journal of the American Ceramic Society, 2015, 98, 1253-1258.	1.9	4
72	Grain boundary interactions in multicrystalline silicon grown from small randomly oriented seeds. Applied Physics Express, 2015, 8, 035502.	1.1	24

#	ARTICLE	IF	CITATIONS
73	Cross-sectional potential profile across a BaSi ₂ pn junction by Kelvin probe force microscopy. Japanese Journal of Applied Physics, 2015, 54, 030306.	0.8	5
74	Reduced thermal degradation of the red-emitting Sr ₂ Si ₅ N ₈ :Eu ²⁺ phosphor via thermal treatment in nitrogen. Journal of Materials Chemistry C, 2015, 3, 7642-7651.	2.7	60
75	Pseudobinary Solid Solution: An Alternative Way for the Bandgap Engineering of Semiconductor Nanowires in the Case of GaP-ZnSe. Advanced Functional Materials, 2015, 25, 2543-2551.	7.8	31
76	Investigation of dislocations in Nb-doped SrTiO ₃ by electron-beam-induced current and transmission electron microscopy. Applied Physics Letters, 2015, 106, 102109.	1.5	10
77	Low-pass secondary electron detector for outlens scanning electron microscopy. Japanese Journal of Applied Physics, 2015, 54, 088001.	0.8	10
78	Origin of recombination activity at small angle grain boundaries in multicrystalline silicon using multi-seed casting growth method. Japanese Journal of Applied Physics, 2015, 54, 08KD16.	0.8	2
79	Synthesis and Crystal Structures of BaLaSi ₂ with cis-trans Si Chains and Ba ₅ LaSi ₆ with Pentagonal Si Rings. Inorganic Chemistry, 2015, 54, 9188-9194.	1.9	2
80	Applicability of the three-dimensional Alexander-Haasen model for the analysis of dislocation distributions in single-crystal silicon. Journal of Crystal Growth, 2015, 411, 49-55.	0.7	11
81	Cathodoluminescence and Photoconductive Characteristics of Single-Crystal Ternary CdS/CdSe/CdS Biaxial Nanobelts. Small, 2015, 11, 1531-1536.	5.2	14
82	Analysis of Dislocation Structures in 4H-SiC by Synchrotron X-ray Topography. IEEJ Transactions on Fundamentals and Materials, 2015, 135, 768-779.	0.2	1
83	Grain boundaries characterization of semiconducting BaSi ₂ thin films on a polycrystalline Si substrate. , 2014, , .		0
84	Potential variation around grain boundaries in BaSi ₂ films grown on multicrystalline silicon evaluated using Kelvin probe force microscopy. Journal of Applied Physics, 2014, 116, .	1.1	8
85	A Multilevel Intermediate-Band Solar Cell by InGaN/GaN Quantum Dots with a Strain-Modulated Structure. Advanced Materials, 2014, 26, 1414-1420.	11.1	40
86	In situ monitoring of stacking fault formation and its carrier lifetime mediation in p-type 4H-SiC. Applied Physics Letters, 2014, 105, 042104.	1.5	9
87	Comparison of slicing-induced damage in hexagonal SiC by wire sawing with loose abrasive, wire sawing with fixed abrasive, and electric discharge machining. Japanese Journal of Applied Physics, 2014, 53, 071301.	0.8	19
88	Effect of Fe impurity on the dislocations in 4H-SiC: Insights from electrical and optical characterization. Japanese Journal of Applied Physics, 2014, 53, 05FG01.	0.8	2
89	Grain growth of cast-multicrystalline silicon grown from small randomly oriented seed crystal. Journal of Crystal Growth, 2014, 401, 717-719.	0.7	30
90	Crystal growth of 50 cm square mono-like Si by directional solidification and its characterization. Journal of Crystal Growth, 2014, 401, 133-136.	0.7	25

#	ARTICLE	IF	CITATIONS
91	Synthesis and cathodoluminescence of Sb/P co-doped GaN nanowires. Journal of Luminescence, 2014, 145, 208-212.	1.5	6
92	Si-based new material for high-efficiency thin film solar cells. , 2014, , .		0
93	Cathodoluminescence Properties of Blue Emitting Eu^{2+} -Doped AlN -Polytypoids for Field-Emission Displays. Journal of the American Ceramic Society, 2014, 97, 339-341.	1.9	3
94	Influence of Si on the particle growth of AlN ceramics. Applied Physics Express, 2014, 7, 115503.	1.1	6
95	A novel and high brightness AlN:Mn ²⁺ red phosphor for field emission displays. Dalton Transactions, 2014, 43, 6120.	1.6	55
96	Contrast analysis of Shockley partial dislocations in 4H-SiC observed by synchrotron Berg-Barrett X-ray topography. Philosophical Magazine, 2014, 94, 1674-1685.	0.7	35
97	Local defect-induced red-shift of cathodoluminescence in individual ZnS nanobelts. Nanoscale, 2014, 6, 12414-12420.	2.8	21
98	Cross-sectional observation of stacking faults in 4H-SiC by KOH etching on nonpolar $\{1\bar{1}00\}$ face, cathodoluminescence imaging, and transmission electron microscopy. Japanese Journal of Applied Physics, 2014, 53, 081301.	0.8	4
99	Local electrical properties of n-AlInAs/i-GaNAs electron channel structures characterized by the probe-electron-beam-induced current technique. Microscopy (Oxford, England), 2014, 63, 161-166.	0.7	3
100	Origin of Yellow-Band Emission in Epitaxially Grown GaN Nanowire Arrays. ACS Applied Materials & Interfaces, 2014, 6, 14159-14166.	4.0	57
101	Thermal stress induced dislocation distribution in directional solidification of Si for PV application. Journal of Crystal Growth, 2014, 408, 19-24.	0.7	35
102	Analysis of the electrical properties of Cr/n-BaSi ₂ Schottky junction and n-BaSi ₂ /p-Si heterojunction diodes for solar cell applications. Journal of Applied Physics, 2014, 115, .	1.1	49
103	Evaluation of minority carrier diffusion length of undoped n-BaSi ₂ epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. Japanese Journal of Applied Physics, 2014, 53, 078004.	0.8	20
104	Cheap, Gram-Scale Fabrication of BN Nanosheets via Substitution Reaction of Graphite Powders and Their Use for Mechanical Reinforcement of Polymers. Scientific Reports, 2014, 4, 4211.	1.6	39
105	Dislocation Generation and Propagation across the Seed in Seed Cast-Si Ingots. Acta Physica Polonica A, 2014, 125, 1024-1026.	0.2	1
106	Focused Ion Beam Imaging of Defects in Multicrystalline Si for Photovoltaic Application. Acta Physica Polonica A, 2014, 125, 991-993.	0.2	1
107	Luminescence properties of a blue-emitting phosphor: (Sr _{1-x} Eu _x)Si ₉ Al ₁₉ O ₃₁ (0<x%1). Journal of Solid State Chemistry, 2013, 207, 49-54.	1.4	14
108	Cathodoluminescence of Self-assembled Nanosystems. , 2013, , 557-601.		2

#	ARTICLE	IF	CITATIONS
109	Evaluation of residual strain in directional solidified mono-Si ingots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 141-145.	0.8	15
110	Crystallography and cathodoluminescence of pyramid-like GaN nanorods epitaxially grown on a sapphire substrate. <i>RSC Advances</i> , 2013, 3, 22914.	1.7	20
111	Butterfly-shaped distribution of SiN precipitates in multi-crystalline Si for solar cells. <i>Journal of Crystal Growth</i> , 2013, 377, 37-42.	0.7	14
112	Ion irradiation induced formation of CdO microcrystals on CdTe surfaces. <i>Materials Letters</i> , 2013, 92, 397-400.	1.3	7
113	Synthesis, Microstructure, and Cathodoluminescence of [0001]-Oriented GaN Nanorods Grown on Conductive Graphite Substrate. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 12066-12072.	4.0	33
114	Solid Solution, Phase Separation, and Cathodoluminescence of GaP/ZnS Nanostructures. <i>ACS Applied Materials & Interfaces</i> , 2013, 5, 9199-9204.	4.0	16
115	Growth Temperature Influence on the Luminescence of Eu,Si-Codoped AlN Phosphors. <i>ECS Journal of Solid State Science and Technology</i> , 2013, 2, R126-R130.	0.9	8
116	Local analysis of Eu ²⁺ emission in CaAlSi ₃ . <i>Science and Technology of Advanced Materials</i> , 2013, 14, 064201.	2.8	18
117	10 cm Diameter Mono Cast Si Growth and its Characterization. <i>Solid State Phenomena</i> , 2013, 205-206, 89-93.	0.3	4
118	Analysis of Inhomogeneous Dislocation Distribution in Multicrystalline Si. <i>Solid State Phenomena</i> , 2013, 205-206, 77-82.	0.3	0
119	Cathodoluminescence Modulation of ZnS Nanostructures by Morphology, Doping, and Temperature. <i>Advanced Functional Materials</i> , 2013, 23, 3701-3709.	7.8	69
120	Evaluation of potential variations around grain boundaries in BaSi ₂ epitaxial films by Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	29
121	Effect of Crystallinity on Residual Strain Distribution in Cast-Grown Si. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 065501.	0.8	11
122	Triangular ZnO Nanosheets: Synthesis, Crystallography and Cathodoluminescence. <i>Journal of Nanoscience and Nanotechnology</i> , 2013, 13, 5744-5749.	0.9	7
123	Emission Enhancement of SiC/SiO ₂ Core/Shell Nanowires Induced by the Oxide Shell. <i>Materials Science Forum</i> , 2012, 717-720, 557-560.	0.3	1
124	Cathodoluminescence study of nonuniformity in hydride vapor phase epitaxy-grown thick GaN films. <i>Journal of Electron Microscopy</i> , 2012, 61, 25-30.	0.9	8
125	Tuning minority-carrier lifetime through stacking fault defects: The case of polytypic SiC. <i>Applied Physics Letters</i> , 2012, 100, .	1.5	20
126	Analysis of the spectra of trivalent erbium in multiple sites of hexagonal aluminum nitride. <i>Optical Materials Express</i> , 2012, 2, 1186.	1.6	6

#	ARTICLE	IF	CITATIONS
127	Influence of substrate nitridation on GaN and InN growth by plasma-assisted molecular-beam epitaxy. Journal of the Ceramic Society of Japan, 2012, 120, 513-519.	0.5	3
128	Characterization of Impurity Doping and Stress in Si/Ge and Ge/Si Core-Shell Nanowires. ACS Nano, 2012, 6, 8887-8895.	7.3	64
129	High-yield boron nitride nanosheets from chemical blowing™: towards practical applications in polymer composites. Journal of Physics Condensed Matter, 2012, 24, 314205.	0.7	40
130	Impact of Light-Element Impurities on Crystalline Defect Generation in Silicon Wafer. Japanese Journal of Applied Physics, 2012, 51, 02BP08.	0.8	7
131	Reduction of polycrystalline grains region near the crucible wall during seeded growth of monocrystalline silicon in a unidirectional solidification furnace. Journal of Crystal Growth, 2012, 352, 47-52.	0.7	55
132	Investigation of grain boundaries in BaSi ₂ epitaxial films on Si(1 1 1) substrates using transmission electron microscopy and electron-beam-induced current technique. Journal of Crystal Growth, 2012, 348, 75-79.	0.7	133
133	Cross sectional CL study of the growth and annihilation of pit type defects in HVPE grown (0001) thick GaN. Journal of Crystal Growth, 2012, 351, 83-87.	0.7	23
134	Fabrication, characterization, cathodoluminescence, and field-emission properties of silica (SiO ₂) nanostructures. Materials Characterization, 2012, 73, 81-88.	1.9	4
135	Evaluation of defects generation in crystalline silicon ingot grown by cast technique with seed crystal for solar cells. Journal of Applied Physics, 2012, 111, 074505.	1.1	24
136	Facile synthesis of vertically aligned hexagonal boron nitride nanosheets hybridized with graphitic domains. Journal of Materials Chemistry, 2012, 22, 4818.	6.7	81
137	Dislocation Analysis of a New Method for Growing Large-Size Crystals of Monocrystalline Silicon Using a Seed Casting Technique. Crystal Growth and Design, 2012, 12, 6144-6150.	1.4	17
138	Anisotropic Thermal Stress Simulation with Complex Crystal-Melt Interface Evolution for Seeded Growth of Monocrystalline Silicon. Crystal Growth and Design, 2012, 12, 5708-5714.	1.4	16
139	Direct imaging and optical activities of stacking faults in 4H-SiC homoepitaxial films. Journal of Applied Physics, 2012, 111, 053513.	1.1	9
140	Secondary electron image formation of a freestanding Si ₃ N ₄ nanobelt. Journal of Applied Physics, 2012, 111, 054316.	1.1	3
141	Deep-level photoluminescence due to dislocations and oxygen precipitates in multicrystalline Si. Journal of Applied Physics, 2012, 111, .	1.1	77
142	Surface defects and accompanying imperfections in 4H-SiC: Optical, structural and electrical characterization. Acta Materialia, 2012, 60, 51-58.	3.8	50
143	Luminescence properties of SiC/SiO ₂ core-shell nanowires with different radial structure. Materials Letters, 2012, 71, 137-140.	1.3	34
144	Impact of Light-Element Impurities on Crystalline Defect Generation in Silicon Wafer. Japanese Journal of Applied Physics, 2012, 51, 02BP08.	0.8	9

#	ARTICLE	IF	CITATIONS
145	Spatially resolved cathodoluminescence of individual BN-coated CaS:Eu nanowires. <i>Nanoscale</i> , 2011, 3, 598-602.	2.8	6
146	Bulk synthesis, growth mechanism and properties of highly pure ultrafine boron nitride nanotubes with diameters of sub-10 nm. <i>Nanotechnology</i> , 2011, 22, 145602.	1.3	97
147	Segregation Behaviors and Radial Distribution of Dopant Atoms in Silicon Nanowires. <i>Nano Letters</i> , 2011, 11, 651-656.	4.5	72
148	Tantalum oxide nanomesh as self-standing one nanometre thick electrolyte. <i>Energy and Environmental Science</i> , 2011, 4, 3509.	15.6	64
149	Crystal growth and characterization of gallium oxynitride nanowires grown on seed crystals. <i>Journal of Crystal Growth</i> , 2011, 337, 87-92.	0.7	8
150	Image instability during the electrical measurement in scanning electron microscope. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1407-1411.	0.8	0
151	Comparison of dislocation behavior in Si and $4H\text{-SiC}$. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1278-1281.	0.8	3
152	Secondary electron imaging of titania thin film for surface potential analysis. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1293-1296.	0.8	1
153	Electrical and optical activities of small angle grain boundaries in multicrystalline Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1347-1350.	0.8	4
154	Luminescent properties of ZnO thin films treated by pulse-modulated high-power inductively coupled plasma. <i>Applied Surface Science</i> , 2011, 257, 7156-7159.	3.1	1
155	Spatial luminescent properties and growth mechanism of one- and two-dimensional ZnO complexes. <i>Journal of Luminescence</i> , 2011, 131, 1082-1085.	1.5	3
156	Effect of Introducing FeSi_2 Template Layers on Defect Density and Minority Carrier Diffusion Length in Si Region near $p\text{-FeSi}_2/n\text{-Si}$ Heterointerface. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 041303.	0.8	0
157	Minority-carrier diffusion length, minority-carrier lifetime, and photoresponsivity of FeSi_2 layers grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2011, 109, 123502.	1.1	11
158	Effect of Introducing FeSi_2 Template Layers on Defect Density and Minority Carrier Diffusion Length in Si Region near $p\text{-FeSi}_2/n\text{-Si}$ Heterointerface. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 041303.	0.8	0
159	Investigation on buffer layer for InN growth by molecular beam epitaxy. <i>Journal of the Ceramic Society of Japan</i> , 2010, 118, 152-156.	0.5	1
160	Effects of Chemical Treatment on the Luminescence of ZnO. <i>Journal of Electronic Materials</i> , 2010, 39, 761-765.	1.0	4
161	Quantitative Photoelastic Characterization of Residual Strains in Grains of Multicrystalline Silicon. <i>Journal of Electronic Materials</i> , 2010, 39, 700-703.	1.0	16
162	Electrical and Optical Properties of Stacking Faults in $4H\text{-SiC}$ Devices. <i>Journal of Electronic Materials</i> , 2010, 39, 684-687.	1.0	14

#	ARTICLE	IF	CITATIONS
163	Effect of Size-Dependent Thermal Instability on Synthesis of Zn ₂ SiO ₄ -SiO _x Core-Shell Nanotube Arrays and Their Cathodoluminescence Properties. <i>Nanoscale Research Letters</i> , 2010, 5, 773-780.	3.1	19
164	ZnS Branched Architectures as Optoelectronic Devices and Field Emitters. <i>Advanced Materials</i> , 2010, 22, 2376-2380.	11.1	96
165	Synthesis and characterization of Zn-doped GaN crystals by simultaneous carbothermal reduction and nitridation of Ga ₂ O ₃ and ZnO. <i>Journal of Crystal Growth</i> , 2010, 312, 452-456.	0.7	5
166	Fabrication of a freestanding GaN layer by direct growth on a ZnO template using hydride vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2010, 312, 2150-2153.	0.7	2
167	Anomalous capacitance-voltage characteristics of Pt-AlGaIn/GaN Schottky diodes exposed to hydrogen. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1928-1930.	0.8	9
168	352 nm ultraviolet emission from high-quality crystalline AlN whiskers. <i>Nanotechnology</i> , 2010, 21, 075708.	1.3	18
169	Enhancement of the core near-band-edge emission induced by an amorphous shell in coaxial one-dimensional nanostructure: the case of SiC/SiO ₂ core/shell self-organized nanowires. <i>Nanotechnology</i> , 2010, 21, 345702.	1.3	37
170	Phase Separation Resulting from Mg Doping in p-InGaIn Film Grown on GaN/Sapphire Template. <i>Applied Physics Express</i> , 2010, 3, 111004.	1.1	29
171	Evidence for a general mechanism modulating carrier lifetime in SiC. <i>Physical Review B</i> , 2010, 81, .	1.1	21
172	Hydrogen released from bulk ZnO single crystals investigated by time-of-flight electron-stimulated desorption. <i>Journal of Applied Physics</i> , 2010, 108, 104902.	1.1	4
173	Pinning of recombination-enhanced dislocation motion in 4H-SiC: Role of Cu and EH1 complex. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	23
174	Structural characterization and cathodoluminescence of individual BN layers-sheathed CaS:Eu nanowires. , 2010, , .		0
175	Pre-existing and process induced defects in high-k gate dielectrics ∼direct observation with EBIC and impact on 1/f noise∼. , 2010, , .		1
176	Inorganically filled carbon nanotubes: Synthesis and properties. <i>Pure and Applied Chemistry</i> , 2010, 82, 2097-2109.	0.9	7
177	(Invited) An Electron-Beam-Induced Current Investigation of Electrical Defects in High-k Gate Stacks. <i>ECS Transactions</i> , 2010, 28, 299-313.	0.3	7
178	Optical and structural properties of SiO ₂ co-doped with Si-nc and Er ³⁺ ions. , 2010, , .		1
179	Unipolar assembly of zinc oxide rods manifesting polarity-driven collective luminescence. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2010, 107, 13588-13592.	3.3	44
180	Low-energy cathodoluminescence microscopy for the characterization of nanostructures. <i>Science and Technology of Advanced Materials</i> , 2010, 11, 043001.	2.8	49

#	ARTICLE	IF	CITATIONS
181	Solution Growth and Cathodoluminescence of Novel SnO ₂ Core-Shell Homogeneous Microspheres. <i>Journal of Physical Chemistry C</i> , 2010, 114, 8235-8240.	1.5	48
182	Doping and Raman Characterization of Boron and Phosphorus Atoms in Germanium Nanowires. <i>ACS Nano</i> , 2010, 4, 3807-3816.	7.3	99
183	Single-crystal MgS nanotubes: synthesis and properties. <i>CrystEngComm</i> , 2010, 12, 1286-1289.	1.3	7
184	Investigation of emitting centers in SiO ₂ codoped with silicon nanoclusters and Er ³⁺ ions by cathodoluminescence technique. <i>Journal of Applied Physics</i> , 2010, 108, 113504.	1.1	21
185	Suppression of concentration quenching of Er-related luminescence in Er-doped GaN. <i>Applied Physics Letters</i> , 2010, 96, 181901.	1.5	33
186	Unpredicted Nucleation of Extended Zinc Blende Phases in Wurtzite ZnO Nanotetrapod Arms. <i>ACS Nano</i> , 2009, 3, 3158-3164.	7.3	49
187	Long wavelength emissions of periodic yard-glass shaped boron nitride nanotubes. <i>Applied Physics Letters</i> , 2009, 94, 023105.	1.5	18
188	Periodic supply of indium as surfactant for N-polar InN growth by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2009, 95, .	1.5	6
189	Trap-Related Carrier Transports in p-Channel Field-Effect Transistor with Polycrystalline Si/HSiON Gate Stack. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 04C005.	0.8	0
190	Electron-beam-induced current and cathodoluminescence study of dislocation arrays in 4H-SiC homoepitaxial layers. <i>Journal of Applied Physics</i> , 2009, 106, .	1.1	23
191	Secondary Electron Imaging of Monolayer Titania Nanosheets. <i>Applied Physics Express</i> , 2009, 2, 105504.	1.1	10
192	Electron-Beam-Induced Current Study of Breakdown Behavior of High-K Gate MOSFETs. <i>Solid State Phenomena</i> , 2009, 156-158, 461-466.	0.3	1
193	Thin-walled boron nitride microtubes exhibiting intense band-edge UV emission at room temperature. <i>Nanotechnology</i> , 2009, 20, 085705.	1.3	45
194	Growth of colorless transparent GaN single crystals on prismatic GaN seeds using a Ga melt and Na vapor. <i>Materials Research Bulletin</i> , 2009, 44, 594-599.	2.7	22
195	Field Emission and Cathodoluminescence of ZnS Hexagonal Pyramids of Zinc Blende Structured Single Crystals. <i>Advanced Functional Materials</i> , 2009, 19, 484-490.	7.8	47
196	Solvothermal Synthesis, Cathodoluminescence, and Field-Emission Properties of Pure and Na-Doped ZnO Nanobullets. <i>Advanced Functional Materials</i> , 2009, 19, 131-140.	7.8	153
197	Characterization, Cathodoluminescence, and Field-Emission Properties of Morphology-Tunable CdS Micro/Nanostructures. <i>Advanced Functional Materials</i> , 2009, 19, 2423-2430.	7.8	114
198	Single-Crystalline ZnS Nanobelts as Ultraviolet-Light Sensors. <i>Advanced Materials</i> , 2009, 21, 2034-2039.	11.1	537

#	ARTICLE	IF	CITATIONS
199	UV Photodetectors: Single-Crystalline ZnS Nanobelts as Ultraviolet-Light Sensors (Adv. Mater.) Tj ETQq1 1 0.784314 rgBT /Oyerlock 10	11.1	10
200	Sharing of secondary electrons by in-lens and out-lens detector in low-voltage scanning electron microscope equipped with immersion lens. Ultramicroscopy, 2009, 109, 368-372.	0.8	43
201	Growth and characterization of isotopic ^{nat} Ga ¹⁵ N by molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S707.	0.8	1
202	Role of Si in the Luminescence of AlN:Eu,Si Phosphors. Journal of the American Ceramic Society, 2009, 92, 1272-1275.	1.9	38
203	Doping and segregation of impurity atoms in silicon nanowires. Physica B: Condensed Matter, 2009, 404, 5200-5202.	1.3	2
204	Electrical activities of stacking faults and partial dislocations in 4H-SiC homoepitaxial films. Superlattices and Microstructures, 2009, 45, 295-300.	1.4	8
205	Comparison between cathodoluminescence spectroscopy and capacitance transient spectroscopy on Al ⁺ ion implanted 4H-SiC p ⁺ /n diodes. Superlattices and Microstructures, 2009, 45, 383-387.	1.4	12
206	Hydrogen desorption effect on cathodoluminescence of ZnO. Superlattices and Microstructures, 2009, 45, 321-325.	1.4	8
207	Effect of hydrogenation on the cathodoluminescence properties of ZnO single crystals. Microelectronics Journal, 2009, 40, 262-264.	1.1	4
208	Low-frequency capacitance-voltage study of hydrogen interaction with Pt-AlGaIn/GaN Schottky barrier diodes. Physica Status Solidi - Rapid Research Letters, 2009, 3, 266-268.	1.2	6
209	Uniform, thin and continuous graphitic carbon tubular coatings on CdS nanowires. Journal of Materials Chemistry, 2009, 19, 1093.	6.7	7
210	Structural characterization and iron detection at ≈ 3 grain boundaries in multicrystalline silicon. Journal of Applied Physics, 2009, 105, 113502.	1.1	53
211	Growth of Bulky Single Crystalline Films of (Zn,Mg)O Alloy Semiconductors by Liquid Phase Epitaxy. Crystal Growth and Design, 2009, 9, 1219-1224.	1.4	9
212	Band Engineering in Strained GaN/ultrathin InN/GaN Quantum Wells. Crystal Growth and Design, 2009, 9, 1698-1701.	1.4	12
213	The synthesis, structure and cathodoluminescence of ellipsoid-shaped ZnGa ₂ O ₄ nanorods. Nanotechnology, 2009, 20, 365705.	1.3	20
214	Cathodoluminescence study of dislocation-related luminescence from small-angle grain boundaries in multicrystalline silicon. Applied Physics Letters, 2009, 94, 112103.	1.5	17
215	Electron beam induced current investigation of stress-induced leakage and breakdown processes in high-k stacks. , 2009, , .		0
216	Growth and characterization of isotopic ^{nat} Ga ¹⁵ N by molecular-beam epitaxy. Proceedings of SPIE, 2009, , .	0.8	0

#	ARTICLE	IF	CITATIONS
217	Carrier Recombination Activities and Structural Properties of Small-Angle Boundaries in Multicrystalline Silicon. <i>Solid State Phenomena</i> , 2008, 131-133, 9-14.	0.3	8
218	Observation of Leakage Sites in High-k Gate Dielectrics in MOSFET Devices by Electron-Beam-Induced Current Technique. <i>Solid State Phenomena</i> , 2008, 131-133, 449-454.	0.3	1
219	Impact of electron beam irradiation on the cathodoluminescence intensity for ZnO and GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 307-310.	1.1	9
220	Electron-beam-induced current study of electrical activity of dislocations in 4H-SiC homoepitaxial film. <i>Journal of Materials Science: Materials in Electronics</i> , 2008, 19, 219-223.	1.1	14
221	Impurity doping in silicon nanowires synthesized by laser ablation. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 93, 589-592.	1.1	11
222	Advanced semiconductor diagnosis by multidimensional electron-beam-induced current technique. <i>Scanning</i> , 2008, 30, 347-353.	0.7	4
223	Growth, Cathodoluminescence and Field Emission of ZnS Tetrapod Tree-like Heterostructures. <i>Advanced Functional Materials</i> , 2008, 18, 3063-3069.	7.8	48
224	Vapor-phase growth of high-quality GaN single crystals in crucible by carbothermal reduction and nitridation of Ga ₂ O ₃ . <i>Journal of Crystal Growth</i> , 2008, 310, 530-535.	0.7	18
225	Luminescence of GaAs/AlGaAs core-shell nanowires grown by MOVPE using tertiarybutylarsine. <i>Journal of Crystal Growth</i> , 2008, 310, 5114-5118.	0.7	35
226	Luminescence properties of Ca- and Yb-codoped SiAlON phosphors. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 146, 80-83.	1.7	13
227	Cathodoluminescence characterization of β -SiC nanowires and surface-related silicon dioxide. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 179-181.	1.9	13
228	Influence of Li-dopants on the luminescent and ferroelectric properties of ZnO thin films. <i>Solid State Communications</i> , 2008, 148, 448-451.	0.9	17
229	Secondary electron emission from freely supported nanowires. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	19
230	Preparation and Cathodoluminescence of Mg-Doped and Zn-Doped GaN Powders. <i>Journal of the American Ceramic Society</i> , 2008, 91, 1711-1714.	1.9	19
231	Novel Boron Nitride Hollow Nanoribbons. <i>ACS Nano</i> , 2008, 2, 2183-2191.	7.3	192
232	InN Growth by Plasma-Assisted Molecular Beam Epitaxy with Indium Monolayer Insertion. <i>Crystal Growth and Design</i> , 2008, 8, 1073-1077.	1.4	7
233	Isotope Effect on Band Gap and Radiative Transitions Properties of Boron Nitride Nanotubes. <i>Nano Letters</i> , 2008, 8, 491-494.	4.5	83
234	Photoluminescence and x-ray diffraction measurements of InN epilayers grown with varying In/N ratio by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2008, 92, 211910.	1.5	5

#	ARTICLE	IF	CITATIONS
235	Self-Assembly and Cathodoluminescence of Microbelts from Cu-Doped Boron Nitride Nanotubes. ACS Nano, 2008, 2, 1523-1532.	7.3	41
236	Structure and Cathodoluminescence of Individual ZnS/ZnO Biaxial Nanobelt Heterostructures. Nano Letters, 2008, 8, 2794-2799.	4.5	185
237	Mapping of extended defects in B-doped (001) homoepitaxial diamond films by electron-beam-induced current (EBIC) and cathodoluminescence (CL) combination technique. Diamond and Related Materials, 2008, 17, 489-493.	1.8	5
238	An n-type silicon nanowire dot based single-electron transistor. , 2008, , .		0
239	Multiangular Branched ZnS Nanostructures with Needle-Shaped Tips: Potential Luminescent and Field-Emitter Nanomaterial. Journal of Physical Chemistry C, 2008, 112, 4735-4742.	1.5	89
240	Luminescence distribution of Yb-doped Ca- \hat{I} -SiAlON phosphors. Journal of Materials Research, 2008, 23, 1701-1705.	1.2	19
241	Electron-beam-induced current study of stacking faults and partial dislocations in 4H-SiC Schottky diode. Applied Physics Letters, 2008, 93, .	1.5	39
242	Secondary electron imaging of embedded defects in carbon nanofiber via interconnects. Applied Physics Letters, 2008, 93, .	1.5	10
243	Sb Surfactant Effect on Defect Evolution in Compressively Strained In _{0.80} Ga _{0.20} As Quantum Well on InP Grown by Metalorganic Vapor Phase Epitaxy. Applied Physics Express, 2008, 1, 111202.	1.1	6
244	Correlation between residual strain and electrically active grain boundaries in multicrystalline silicon. Applied Physics Letters, 2008, 93, .	1.5	34
245	Evaluation of minority-carrier diffusion length in n-type \hat{I}^2 -FeSi ₂ single crystals by electron-beam-induced current. Applied Physics Letters, 2008, 92, 042117.	1.5	16
246	Lifetime and diffusion length of photogenerated minority carriers in single-crystalline n-type \hat{I}^2 -FeSi ₂ bulk. Applied Physics Letters, 2008, 92, 192114.	1.5	17
247	Codoping of boron and phosphorus in silicon nanowires synthesized by laser ablation. Applied Physics Letters, 2008, 93, .	1.5	33
248	Comparison of leakage behaviors in p- and n-type metal-oxide-semiconductor capacitors with hafnium silicon oxynitride gate dielectric by electron-beam-induced current. Applied Physics Letters, 2008, 92, 262103.	1.5	4
249	Classical Coulomb blockade of a silicon nanowire dot. Applied Physics Letters, 2008, 92, 213110.	1.5	16
250	Silver-Deposited Polydiacetylene Nanocrystals Produced by Visible-Light-Driven Photocatalytic Reduction. Japanese Journal of Applied Physics, 2007, 46, L336-L338.	0.8	14
251	Enhanced red electroluminescence from a polycrystalline diamond film/Si heterojunction structure. Applied Physics Letters, 2007, 90, 161123.	1.5	9
252	Blue emission of Ce ³⁺ in lanthanide silicon oxynitride phosphors. Journal of Materials Research, 2007, 22, 1933-1941.	1.2	86

#	ARTICLE	IF	CITATIONS
253	Isotope effects between hydrogen and deuterium microwave plasmas on chemical vapor deposition homoepitaxial diamond growth. <i>Journal of Applied Physics</i> , 2007, 101, 103501.	1.1	10
254	Spatial Distribution of Impurities in ZnO Nanotubes Characterized by Cathodoluminescence. <i>Journal of Nanoscience and Nanotechnology</i> , 2007, 7, 3323-3327.	0.9	24
255	Electron Beam Nanoprocessing of a Carbon Nanotube Film Using a Variable Pressure Scanning Electron Microscope. <i>Journal of Nanoscience and Nanotechnology</i> , 2007, 7, 2356-2360.	0.9	1
256	ZnO Films Grown on Si Substrates with Au Nanocrystallites as Nuclei. <i>Crystal Growth and Design</i> , 2007, 7, 564-568.	1.4	7
257	Carrier Recombination Activity and Structural Properties of Small-Angle Grain Boundaries in Multicrystalline Silicon. <i>Japanese Journal of Applied Physics</i> , 2007, 46, 6489-6497.	0.8	103
258	Phosphorus doping and hydrogen passivation of donors and defects in silicon nanowires synthesized by laser ablation. <i>Applied Physics Letters</i> , 2007, 90, 153117.	1.5	42
259	Synthesis and Characterization of Ge-Doped GaN Crystalline Powders Deposited on Graphite and Silica Glass Substrates. <i>Crystal Growth and Design</i> , 2007, 7, 1251-1255.	1.4	7
260	Tailoring the Optical Properties of Epitaxially Grown Biaxial ZnO/Ge, and Coaxial ZnO/Ge/ZnO and Ge/ZnO/Ge Heterostructures. <i>Advanced Functional Materials</i> , 2007, 17, 270-276.	7.8	54
261	High-Yield Synthesis of Rhombohedral Boron Nitride Triangular Nanoplates. <i>Advanced Materials</i> , 2007, 19, 2141-2144.	11.1	61
262	Luminescence of GaN single crystals prepared by heating a Ga melt in N ₂ atmosphere. <i>Crystal Research and Technology</i> , 2007, 42, 713-717.	0.6	1
263	Growth and characterization of millimeter-sized GaN crystals by carbothermal reduction and nitridation of Ga ₂ O ₃ . <i>Journal of Crystal Growth</i> , 2007, 299, 22-27.	0.7	18
264	The influence of indium monolayer insertion on the InN epilayer grown by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007, 301-302, 521-524.	0.7	2
265	Electron-beam-induced current study of grain boundaries in multicrystalline Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2908-2917.	0.8	20
266	Photoinduced Charge Injection and Bandgap-Engineering of High-Specific-Surface-Area BN Nanotubes using a Zinc Phthalocyanine Monolayer. <i>Small</i> , 2007, 3, 1330-1335.	5.2	10
267	Growth of ZnS nano-crystallites in gel and their characterization. <i>Materials Chemistry and Physics</i> , 2007, 105, 250-252.	2.0	9
268	Cathodoluminescence and its mapping of flower-like ZnO, ZnO/ZnS core-shell and tube-like ZnS nanostructures. <i>Materials Research Bulletin</i> , 2007, 42, 1286-1292.	2.7	14
269	Luminescence investigations of cubic boron nitride doped with beryllium. <i>Physics of the Solid State</i> , 2007, 49, 1884-1890.	0.2	5
270	Enhancement and patterning of ultraviolet emission in ZnO with an electron beam. <i>Applied Physics Letters</i> , 2006, 88, 134103.	1.5	103

#	ARTICLE	IF	CITATIONS
271	Precise Fabrication of Point Defects in Self-Assembled Three-Dimensional Macroporous Photonic Crystals. <i>Journal of Physical Chemistry B</i> , 2006, 110, 1107-1110.	1.2	14
272	Low-Temperature Growth of Uniform ZnO Particles with Controllable Ellipsoidal Morphologies and Characteristic Luminescence Patterns. <i>Journal of Physical Chemistry B</i> , 2006, 110, 19147-19153.	1.2	56
273	Doping and hydrogen passivation of boron in silicon nanowires synthesized by laser ablation. <i>Applied Physics Letters</i> , 2006, 89, 203109.	1.5	55
274	é»âç.šè`èµ.é»æµ•(EBIC) æ³•ã, 'ç””ã,ãŸãšçµæ™¶ã,ãf³ã,3ãf³ã«ãšãã,ç²'ç•CEã®é»æ°—çš,,æ»æ€\$ã° è©•ã¼j. <i>Material Japan</i> , 2006, 45,		
275	Cathodoluminescence characterization of ZnO nanotubes grown by MOCVD on sapphire substrate. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 146-150.	1.9	24
276	Defect influence on luminescence efficiency of GaN-based LEDs. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 371-374.	1.9	6
277	Cathodoluminescence characterization of SnO ₂ nanoribbons grown by vapor transport technique. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 331-336.	1.9	9
278	Recombination behavior of nickel in cast multicrystalline silicon. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 304-307.	1.9	7
279	Effect of the oblique excitation and detection on the cathodoluminescence spectra. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 19-24.	1.9	0
280	Control of single supramolecular chain of porphyrin on a copper surface. <i>Thin Solid Films</i> , 2006, 499, 329-332.	0.8	16
281	Cathodoluminescence characterization of GaN quantum dots grown on 6H-SiC substrate by metal-organic chemical vapor deposition. <i>Scripta Materialia</i> , 2006, 55, 679-682.	2.6	4
282	Hollow and Polygonous Microtubes of Monocrystalline Indium Germanate. <i>Angewandte Chemie - International Edition</i> , 2006, 45, 228-231.	7.2	30
283	Single-Crystal Nanotubes of II-VI Semiconductors. <i>Angewandte Chemie - International Edition</i> , 2006, 45, 7568-7572.	7.2	82
284	Silica Fibers with Triangular Cross Sections. <i>Advanced Materials</i> , 2006, 18, 1852-1856.	11.1	5
285	Nanoprocessing of Diamond Using a Variable Pressure Scanning Electron Microscope. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L71-L73.	0.8	15
286	Silver-Coated Polydiacetylene Nanocrystals Fabricated Using Surfactants as Binder. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 379-383.	0.8	14
287	Thermal-desorption induced enhancement and patterning of ultraviolet emission in chemically grown ZnO. <i>Nanotechnology</i> , 2006, 17, 2789-2793.	1.3	24
288	Carrier Doping of Silicon Nanowires Synthesized by Laser Ablation. <i>Materials Research Society Symposia Proceedings</i> , 2006, 963, 1.	0.1	0

#	ARTICLE	IF	CITATIONS
289	Near-Infrared Light Emission from of Er-Doped ZnO Thin Film in Micropits Processed on Si Substrate. Key Engineering Materials, 2006, 320, 113-116.	0.4	0
290	Observation of leakage sites in a hafnium silicon oxynitride gate dielectric of a metal-oxide-semiconductor field-effect transistor device by electron-beam-induced current. Applied Physics Letters, 2006, 89, 222104.	1.5	13
291	Single-crystalline cubic structured InP nanosprings. Applied Physics Letters, 2006, 88, 243106.	1.5	36
292	Cathodoluminescence Study of Semiconductor Nanostructures. Materia Japan, 2006, 45, 899-899.	0.1	0
293	Electrical activity of grain boundaries in polycrystalline silicon – influences of grain boundary structure, chemistry and temperature. International Journal of Materials Research, 2005, 96, 197-206.	0.8	9
294	Characterization of homoepitaxial and heteroepitaxial ZnO films grown by pulsed laser deposition. Applied Surface Science, 2005, 244, 377-380.	3.1	13
295	Electron-beam-induced current study of hydrogen passivation on grain boundaries in multicrystalline silicon: Influence of GB character and impurity contamination. Physica B: Condensed Matter, 2005, 364, 162-169.	1.3	39
296	Structure and properties of GaN films grown on single crystalline ZnO substrates by molecular beam epitaxy. Journal of Crystal Growth, 2005, 275, e1143-e1148.	0.7	17
297	Low-temperature growth of GaN microcrystals from position-controlled Ga droplets arrayed by a low-energy focused ion beam system. Journal of Crystal Growth, 2005, 283, 328-331.	0.7	3
298	GaN nanodot fabrication by implant source growth. Microelectronics Journal, 2005, 36, 456-459.	1.1	3
299	Strong Green Emission from β -SiAlON Activated by Divalent Ytterbium under Blue Light Irradiation. Journal of Physical Chemistry B, 2005, 109, 9490-9494.	1.2	138
300	Processing of carbon nanotubes with electron beams in gas atmospheres. Scripta Materialia, 2005, 53, 703-705.	2.6	5
301	Single-Catalyst Confined Growth of ZnS/Si Composite Nanowires. Advanced Materials, 2005, 17, 225-230.	11.1	39
302	Self-Assembly of SiO ₂ Nanowires and Si Microwires into Hierarchical Heterostructures on a Large Scale. Advanced Materials, 2005, 17, 971-975.	11.1	87
303	Aligned Zn ²⁺ /Zn ₂ SiO ₄ Core/Shell Nanocables with Homogeneously Intense Ultraviolet Emission at 300 nm.. ChemInform, 2005, 36, no.	0.1	0
304	Comparison between Electron Beam and Near-Field Light on the Luminescence Excitation of GaAs/AlGaAs Semiconductor Quantum Dots. Japanese Journal of Applied Physics, 2005, 44, 1820-1824.	0.8	3
305	Nonpolar a-plane GaN film on Si(100) produced using a specially designed lattice-matched buffer: A fresh approach to eliminate the polarization effect. Journal of Applied Physics, 2005, 97, 043531.	1.1	9
306	Recombination activity of Γ boundaries in boron-doped multicrystalline silicon: Influence of iron contamination. Journal of Applied Physics, 2005, 97, 033701.	1.1	84

#	ARTICLE	IF	CITATIONS
307	Single-crystalline nanotubes of IIB-VI semiconductors. Applied Physics Letters, 2005, 87, 113107.	1.5	46
308	ZnO Light-Emission Array Fabricated into Nanometer-scale Pits on Silicon Substrate. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	0
309	Inhomogeneous distribution of dislocations in a SiGe graded layer and its influence on surface morphology and misfit dislocations at the interface of strained Si ^{1-x} Si _{0.8} Ge _{0.2} . Applied Physics Letters, 2005, 86, 162102.	1.5	11
310	Large-scale fabrication of boron nitride nanohorn. Applied Physics Letters, 2005, 87, 063107.	1.5	42
311	Aligned Zn ²⁺ /Zn ₂ SiO ₄ Core-Shell Nanocables with Homogenously Intense Ultraviolet Emission at 300 nm. Journal of Physical Chemistry B, 2005, 109, 15786-15790.	1.2	22
312	Porous BCN Nanotubular Fibers: Growth and Spatially Resolved Cathodoluminescence. Journal of the American Chemical Society, 2005, 127, 16354-16355.	6.6	77
313	Yellowish-white luminescence in codoped zinc oxide. Applied Physics Letters, 2005, 86, 091902.	1.5	61
314	Non-equilibrium defects in aluminum-doped zinc oxide thin films grown with a pulsed laser deposition method. Journal of Materials Research, 2005, 20, 2866-2872.	1.2	42
315	Characterization of p-n junction formed at the boundary of facets in cubic-BN using scanning electron microscope. Diamond and Related Materials, 2005, 14, 1955-1959.	1.8	4
316	Characterization and properties of green-emitting β -SiAlON:Eu ²⁺ powder phosphors for white light-emitting diodes. Applied Physics Letters, 2005, 86, 211905.	1.5	656
317	Perfectly Dissolved Boron Nitride Nanotubes Due to Polymer Wrapping. Journal of the American Chemical Society, 2005, 127, 15996-15997.	6.6	248
318	Cathodoluminescence investigation of organic materials. Microscopy (Oxford, England), 2005, 54, 325-330.	0.7	30
319	Cathodoluminescence imaging for identifying uptaken fluorescence materials in Kupffer cells using scanning electron microscopy. Archives of Histology and Cytology, 2004, 67, 263-270.	0.2	16
320	Two-dimensional extremely thin single-crystalline β -Si ₃ N ₄ microribbons. Applied Physics Letters, 2004, 84, 804-806.	1.5	26
321	V defects of ZnO thin films grown on Si as an ultraviolet optical path. Applied Physics Letters, 2004, 84, 502-504.	1.5	25
322	Fabrication of Polydiacetylene Nanocrystals Deposited with Silver Nanoparticles for a Nonlinear Optical Material. Materials Research Society Symposia Proceedings, 2004, 846, DD10.7.1.	0.1	1
323	Ion-Implantation Induced Defects in ZnO Studied by a Slow Positron Beam. Materials Science Forum, 2004, 445-446, 57-59.	0.3	3
324	Effect of Postdeposition Annealing on Luminescence from Zinc Oxide Patterns Prepared by the Electroless Deposition Process. Journal of the Electrochemical Society, 2004, 151, H169.	1.3	24

#	ARTICLE	IF	CITATIONS
325	Synthesis of Crystalline Silicon Tubular Nanostructures with ZnS Nanowires as Removable Templates. <i>Angewandte Chemie - International Edition</i> , 2004, 43, 63-66.	7.2	121
326	Growth of Single-Crystalline Cubic GaN Nanotubes with Rectangular Cross-Sections. <i>Advanced Materials</i> , 2004, 16, 1465-1468.	11.1	50
327	New Boron Nitride Whiskers: Showing Strong Ultraviolet and Visible Light Luminescence.. <i>ChemInform</i> , 2004, 35, no.	0.1	0
328	Uniform Micro-Sized β - and γ -Si ₃ N ₄ Thin Ribbons Grown by a High-Temperature Thermal-Decomposition/Nitridation Route. <i>Chemistry - A European Journal</i> , 2004, 10, 554-558.	1.7	36
329	Flux growth of ZnS single crystals and their characterization. <i>Journal of Crystal Growth</i> , 2004, 267, 74-79.	0.7	3
330	Detection of misfit dislocations at interface of strained Si/Si _{0.8} Ge _{0.2} by electron-beam-induced current technique. <i>Applied Physics Letters</i> , 2004, 84, 3316-3318.	1.5	18
331	Characterisation of nitrogen-implanted CVD homoepitaxial diamond. <i>Diamond and Related Materials</i> , 2004, 13, 600-603.	1.8	7
332	New Boron Nitride Whiskers: Showing Strong Ultraviolet and Visible Light Luminescence. <i>Journal of Physical Chemistry B</i> , 2004, 108, 6193-6196.	1.2	63
333	Electron-beam-induced current study of grain boundaries in multicrystalline silicon. <i>Journal of Applied Physics</i> , 2004, 96, 5490-5495.	1.1	226
334	Low-temperature orientation-selective growth and ultraviolet emission of single-crystal ZnO nanowires. <i>Applied Physics Letters</i> , 2004, 84, 3358-3360.	1.5	103
335	Molten metal flux growth and properties of CrSi ₂ . <i>Journal of Alloys and Compounds</i> , 2004, 383, 319-321.	2.8	12
336	Cathodoluminescence study of one-dimensional free-standing widegap-semiconductor nanostructures: GaN nanotubes, Si ₃ N ₄ nanobelts and ZnS/Si nanowires. <i>Journal of Electron Microscopy</i> , 2004, 53, 203-208.	0.9	16
337	Observation of polarization property in near-field optical imaging by a polarization-maintaining fiber probe. <i>Journal of Electron Microscopy</i> , 2004, 53, 209-215.	0.9	8
338	Two-dimensional micrometer-sized single-crystalline ZnO thin nanosheets. <i>Applied Physics Letters</i> , 2003, 83, 4414-4416.	1.5	194
339	Microwave plasma growth and high spatial resolution cathodoluminescent spectrum of tetrapod ZnO nanostructures. <i>Journal of Solid State Chemistry</i> , 2003, 173, 109-113.	1.4	17
340	Low-energy charge-transfer state and optical properties of Eu ³⁺ -doped GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2639-2643.	0.8	8
341	Passivation of active recombination centers in ZnO by hydrogen doping. <i>Journal of Applied Physics</i> , 2003, 93, 6386-6392.	1.1	107
342	High pressure synthesis of UV-light emitting cubic boron nitride single crystals. <i>Diamond and Related Materials</i> , 2003, 12, 1098-1102.	1.8	49

#	ARTICLE	IF	CITATIONS
343	Blue and ultraviolet cathodoluminescence from Mn-doped epitaxial ZnO thin films. Applied Physics Letters, 2003, 83, 39-41.	1.5	105
344	Epitaxial Heterostructures: Side-to-Side ZnS, ZnSe Biaxial Nanowires, and Sandwichlike ZnS/ZnS Triaxial Nanowires. Journal of the American Chemical Society, 2003, 125, 11306-11313.	6.6	124
345	Postgrowth annealing of defects in ZnO studied by positron annihilation, x-ray diffraction, Rutherford backscattering, cathodoluminescence, and Hall measurements. Journal of Applied Physics, 2003, 94, 4807.	1.1	159
346	Crystal Size Dependence of Fluorescence Spectra from Perylene Nanocrystals Evaluated by Scanning Near-Field Optical Microspectroscopy. Japanese Journal of Applied Physics, 2003, 42, L111-L113.	0.8	54
347	Green emission from c-axis oriented AlN nanorods doped with Tb. Applied Physics Letters, 2003, 83, 4939-4941.	1.5	25
348	High-Temperature Solution Growth and Characterization of Chromium Disilicide. Japanese Journal of Applied Physics, 2003, 42, 7292-7293.	0.8	3
349	Cathodoluminescence study of AlGaAs/GaAs multilayers grown on ridge-type triangles on GaAs (111)A substrates. Journal of Electron Microscopy, 2003, 52, 383-389.	0.9	3
350	PROPERTIES OF ZnO NANOTETRAPODS. , 2003, , .		0
351	Characterization of a diamond p-n junction using electron-beam-induced current and cathodoluminescence. Applied Physics Letters, 2002, 81, 1987-1989.	1.5	28
352	Ultraviolet light emission from self-organized n domains in cubic boron nitride bulk single crystals grown under high pressure. Applied Physics Letters, 2002, 81, 4145-4147.	1.5	48
353	PROPERTIES OF ZnO NANOTETRAPODS. International Journal of Nanoscience, 2002, 01, 515-519.	0.4	1
354	Passivation of Defects in ZnO by Hydrogen Plasma Irradiation. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	1
355	Band-edge emission of undoped and doped ZnO single crystals at room temperature. Journal of Applied Physics, 2002, 91, 3658-3663.	1.1	55
356	Effect of hydrogen doping on ultraviolet emission spectra of various types of ZnO. Applied Physics Letters, 2002, 80, 2869-2871.	1.5	176
357	Low-Temperature Fabrication of Light-Emitting Zinc Oxide Micropatterns Using Self-Assembled Monolayers. Advanced Materials, 2002, 14, 418-421.	11.1	517
358	Cathodoluminescence study of GaN and GaN single crystals grown by a Na or K flux. Science and Technology of Advanced Materials, 2002, 3, 91-94.	2.8	6
359	Effects of Hydrogen Sulfide on the Plasma-assisted Chemical Vapor Deposition of Carbon Nanotubes.. Hyomen Kagaku, 2002, 23, 720-725.	0.0	1
360	Effects of Hydrogen on the Deep Levels in Si, ZnO and Diamond Studied by Cathodoluminescence. Materials Research Society Symposia Proceedings, 2002, 719, 921.	0.1	0

#	ARTICLE	IF	CITATIONS
361	High throughput fabrication of transition-metal-doped epitaxial ZnO thin films: A series of oxide-diluted magnetic semiconductors and their properties. Applied Physics Letters, 2001, 78, 3824-3826.	1.5	575
362	Origin of band-A emission in homoepitaxial diamond films. Diamond and Related Materials, 2001, 10, 526-530.	1.8	17
363	Cathodoluminescence of undoped $\hat{2}$ -Ga ₂ O ₃ single crystals. Solid State Communications, 2001, 120, 455-458.	0.9	92
364	Variation of electrical properties on growth sectors of ZnO single crystals. Journal of Crystal Growth, 2001, 229, 98-103.	0.7	38
365	Defect Characteristics in Sulfur-Implanted CVD Homoepitaxial Diamond. Solid State Phenomena, 2001, 78-79, 171-176.	0.3	2
366	Excitonic Emission from High-Quality Homoepitaxial Diamond Film. Solid State Phenomena, 2001, 78-79, 165-170.	0.3	3
367	Defects Analysis of Diamond Films in Cross Section Using Cathodoluminescence and High-Resolution Transmission Electron Microscopy. Solid State Phenomena, 2001, 78-79, 197-204.	0.3	0
368	Cathodoluminescence microscopy of hydrothermal and flux grown ZnO single crystals. Journal Physics D: Applied Physics, 2001, 34, 2945-2949.	1.3	38
369	Scanning tunnelling spectroscopy characterization of ZnO single crystals. Semiconductor Science and Technology, 2001, 16, 589-593.	1.0	13
370	Defects in 30 keV Er ⁺ -implanted SiO ₂ /Si studied by positron annihilation and cathodoluminescence. Journal of Applied Physics, 2001, 90, 237-242.	1.1	5
371	Trench-type narrow InGaAs quantum wires fabricated on a (311)A InP substrate. Applied Physics Letters, 2001, 78, 76-78.	1.5	24
372	HRTEM and CL Investigation of Defects in High-quality CVD Diamond Films. Materia Japan, 2001, 40, 1031-1031.	0.1	0
373	Effects of hydrogen ion bombardment and boron doping on (001) polycrystalline diamond films. Journal of Crystal Growth, 2000, 213, 328-333.	0.7	9
374	Growth of GaN single crystals from a Na ⁺ Ga melt at 750 ^o C and 5MPa of N ₂ . Journal of Crystal Growth, 2000, 218, 7-12.	0.7	68
375	Hetero-epitaxial growth of ZnO thin films by atmospheric pressure CVD method. Journal of Crystal Growth, 2000, 221, 431-434.	0.7	104
376	Electron-beam-induced-current study of artificial twist boundaries in bonded Si wafers. Journal of Crystal Growth, 2000, 210, 90-93.	0.7	11
377	Zinc-Blende-Type Cubic GaN Single Crystals Prepared in a Potassium Flux. Japanese Journal of Applied Physics, 2000, 39, L146-L148.	0.8	22
378	Surfaces of undoped and boron doped polycrystalline diamond films influenced by negative DC bias voltage. Diamond and Related Materials, 2000, 9, 1636-1639.	1.8	5

#	ARTICLE	IF	CITATIONS
379	Yellow Emission from Zinc Oxide giving an Electron Spin Resonance Signal at $g=1.96$. Japanese Journal of Applied Physics, 1999, 38, L113-L115.	0.8	42
380	Title is missing!. Journal of Materials Science, 1999, 7, 197-205.	1.2	68
381	InGaAs quantum dots formed in tetrahedral-shaped recesses on GaAs (111)B grown by metalorganic chemical vapor deposition. Journal of Electronic Materials, 1999, 28, 466-480.	1.0	4
382	Growth and time-resolved photoluminescence study of self-organized CdSe quantum dots in ZnSe. Superlattices and Microstructures, 1999, 25, 119-125.	1.4	19
383	Homoepitaxial diamond film with an atomically flat surface over a large area. Diamond and Related Materials, 1999, 8, 1272-1276.	1.8	100
384	Impact of Grain Boundary Character on Electrical Property in Polycrystalline Silicon. Materials Research Society Symposia Proceedings, 1999, 586, 163.	0.1	14
385	Development of Low Energy Cathodoluminescence System and its Application to the Study of ZnO Powders. Materials Research Society Symposia Proceedings, 1999, 588, 75.	0.1	15
386	A Study of the Origin of Band-A Emission in Homoepitaxial Diamond Thin Films. Materials Research Society Symposia Proceedings, 1999, 588, 87.	0.1	0
387	Morphology and characterization of GaN single crystals grown in a Na flux. Journal of Crystal Growth, 1998, 186, 8-12.	0.7	125
388	Diamond films epitaxially grown by step-flow mode. Journal of Crystal Growth, 1998, 183, 338-346.	0.7	46
389	Atomic force microscopy study of atomically flat (001) diamond surfaces treated with hydrogen plasma. Applied Surface Science, 1998, 125, 120-124.	3.1	26
390	EBIC and Cathodoluminescence Study of the Bonded Silicon Wafers. Solid State Phenomena, 1998, 63-64, 481-488.	0.3	2
391	Spatially Resolved Cathodoluminescence Study on CVD Homoepitaxial Diamond Film. Solid State Phenomena, 1998, 63-64, 489-496.	0.3	5
392	Cathodoluminescence Study on ZnO and GaN. Solid State Phenomena, 1998, 63-64, 171-182.	0.3	7
393	Orientation dependence of strained ZnSe/ZnS(h11) single quantum well luminescence. Journal of Applied Physics, 1998, 83, 4272-4278.	1.1	6
394	Strong excitonic recombination radiation from homoepitaxial diamond thin films at room temperature. Applied Physics Letters, 1998, 73, 981-983.	1.5	92
395	Cathodoluminescence study of InGaAs/GaAs quantum dot structures formed on the tetrahedral-shaped recesses on GaAs (111)B substrates. Journal of Applied Physics, 1998, 83, 4944-4950.	1.1	15
396	Localization and thermal escape of excitons in ultrathin ZnSe/ZnS single quantum wells linked to interfacial ZnSe quantum slabs. Journal of Applied Physics, 1998, 83, 6028-6033.	1.1	2

#	ARTICLE	IF	CITATIONS
397	Effects of As ₂ Flux and Atomic Hydrogen Irradiation for Growth of InGaAs Quantum Wires by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1998, 37, 1497-1500.	0.8	22
398	Effect of Hydrogenation on ZnO Luminescence. Japanese Journal of Applied Physics, 1997, 36, L289-L291.	0.8	139
399	Gettering of Fe impurities by bulk stacking faults in Czochralski-grown silicon. Applied Physics Letters, 1997, 70, 1876-1878.	1.5	20
400	Formation and Relaxation of Hydrogen-Related Defects in the Subsurface Region of Diamond Films. Materials Science Forum, 1997, 258-263, 745-750.	0.3	4
401	Emission and Capture Kinetics for a Hydrogen-Related Negative-U Center in Silicon: Evidence for Metastable Neutral Charge State. Materials Science Forum, 1997, 258-263, 217-222.	0.3	16
402	Hydrogenation of Deep Defect States in n-Type Si Containing Extended Defects and Transition Metal (Ni) Tj ETQq0 0.0 rgBT /Qverlock 1	0.3	4
403	Cathodoluminescence Study on the Hydrogenation of ZnO Luminescence. Materials Science Forum, 1997, 258-263, 1371-1376.	0.3	4
404	Hydrogenation of Copper Related Deep States in n-Type Si Containing Extended Defects. Materials Science Forum, 1997, 258-263, 319-324.	0.3	3
405	Investigation of the effect of hydrogen on electrical and optical properties in chemical vapor deposited on homoepitaxial diamond films. Journal of Applied Physics, 1997, 81, 744-753.	1.1	254
406	Hydrogen-related gap states in the near surface of chemical vapor deposited homoepitaxial diamond films. Diamond and Related Materials, 1997, 6, 303-307.	1.8	24
407	Self-Organized Growth of II-VI Wide Bandgap Quantum Dot Structures. Physica Status Solidi (B): Basic Research, 1997, 202, 827-833.	0.7	15
408	Hydrogen-Induced Luminescent States In The Subsurface Region Of Homoepitaxial Diamond Films. Materials Research Society Symposia Proceedings, 1996, 442, 699.	0.1	17
409	Cathodoluminescence and EBIC study on misfit dislocations in SiGe/Si heterostructure. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 141-145.	1.7	6
410	EBIC study on the electrical activity of stacking faults in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 235-239.	1.7	12
411	Precipitation of Cu, Ni, and Fe on Frank-Type Partial Dislocations in Czochralski-Grown Silicon. Physica Status Solidi A, 1996, 155, 321-332.	1.7	10
412	Cathodoluminescence study on dislocations in silicon. Journal of Applied Physics, 1996, 79, 3253-3260.	1.1	63
413	Precipitation behaviors of Cu and Fe on Frank-type partial dislocations in Czochralski-grown silicon. Applied Physics Letters, 1996, 68, 214-216.	1.5	15
414	Direct observation of hydrogen-related luminescent states in subsurface region of homoepitaxial diamond films. Applied Physics Letters, 1996, 69, 1122-1124.	1.5	17

#	ARTICLE	IF	CITATIONS
415	Precipitation of Cu and Fe in Dislocated Floating-Zone-Grown Silicon. Japanese Journal of Applied Physics, 1996, 35, 3301-3305.	0.8	31
416	Influences of Cu and Fe Impurities on Oxygen Precipitation in Czochralski-Grown Silicon. Japanese Journal of Applied Physics, 1996, 35, 4187-4194.	0.8	19
417	Electrical activity of extended defects and gettering of metallic impurities in silicon. Materials Science and Technology, 1995, 11, 685-690.	0.8	41
418	Cathodoluminescence from fractured surfaces of ZnO varistors. Journal of Applied Physics, 1995, 77, 4021-4023.	1.1	24
419	Quantitative electron-beam tester for defects in semiconductors (CL/EBIC/SDLTS system). Review of Scientific Instruments, 1995, 66, 4277-4282.	0.6	110
420	Damage-induced luminescence in InP. Applied Physics Letters, 1995, 67, 3777-3779.	1.5	11
421	Electronic states associated with dislocations in p-type silicon studied by means of electric-dipole spin resonance and deep-level transient spectroscopy. Physical Review B, 1995, 51, 16721-16727.	1.1	23
422	Thermal and Optical Emission Processes of Electrons and Holes from EL2 in N- and P-Type GaAs. Materials Science Forum, 1995, 196-201, 261-266.	0.3	0
423	Cathodoluminescence Study on Dislocation-Related Luminescence in Silicon. Materials Science Forum, 1995, 196-201, 1201-1206.	0.3	10
424	Electronic States Associated with Straight Dislocations in P-Type Silicon Studied by Means of Electric-Dipole Spin Resonance. Materials Science Forum, 1995, 196-201, 1189-1194.	0.3	1
425	Metastability and Negative-U Properties for Hydrogen-Related Radiation-Induced Defect in Silicon. Materials Science Forum, 1995, 196-201, 945-950.	0.3	12
426	Precipitation of Cu, Ni and Fe on Frank-Type Partial Dislocations in Czochralski-Grown Silicon. Materials Science Forum, 1995, 196-201, 1207-1212.	0.3	6
427	Hydrogen effect on the optical activity of dislocations in silicon introduced at room temperature. Journal of Applied Physics, 1994, 76, 7882-7888.	1.1	34
428	Study of surface microtopography of InAlAs/InP heterostructures grown by MBE. Solid State Communications, 1994, 92, 983-985.	0.9	0
429	Gettering of copper by bulk stacking faults and punched-out dislocations in Czochralski-grown silicon. Journal of Applied Physics, 1994, 76, 4540-4546.	1.1	75
430	Difference of the electrical properties of screw and 60° dislocations in silicon as detected with temperature-dependent electron beam induced current technique. Applied Physics Letters, 1992, 61, 792-794.	1.5	17
431	CATHODOLUMINESCENCE RELATED TO DISLOCATIONS IN GaAs. , 1990, , 1477-1481.		3
432	Interaction between Dislocations and Non-Radiative Recombination Centers in GaAs. Japanese Journal of Applied Physics, 1987, 26, L179-L182.	0.8	20

#	ARTICLE	IF	CITATIONS
433	Observation of Magnetic Domain Walls in Co and Co-Fe by Differential-Phase-Contrast STEM. Japanese Journal of Applied Physics, 1985, 24, 1229-1233.	0.8	2
434	Magnetic Domain Structure of Fe ₃ Al Alloy with Two-Phase Mixture Studied by Lorentz Microscopy. Japanese Journal of Applied Physics, 1985, 24, 1632-1636.	0.8	1
435	Magnetic Properties of Fe ₃ A+I Single Crystal for B2 and DO ₃ Structures. IEEE Translation Journal on Magnetism in Japan, 1985, 1, 550-551.	0.1	0
436	Magnetic Properties for Fe ₃ Al Single Crystal of the Two Regions with $\hat{1}\pm + B2$ and $\hat{1}\pm + DO_3$ Structures. IEEE Translation Journal on Magnetism in Japan, 1985, 1, 552-553.	0.1	0
437	Study of the Temperature Dependence of the Magnetization Direction in Cobalt Single Crystals by 1 MV Lorentz Electron Microscopy. Japanese Journal of Applied Physics, 1982, 21, L179-L181.	0.8	9
438	EBIC Analysis of Breakdown Failure Point in 4H-SiC PIN Diodes. Materials Science Forum, 0, 615-617, 707-710.	0.3	3
439	Grain Boundaries in Multicrystalline Si. Solid State Phenomena, 0, 156-158, 19-26.	0.3	9
440	D-Line Emission from Small Angle Grain Boundaries in Multicrystalline Si. Solid State Phenomena, 0, 156-158, 561-565.	0.3	0
441	Nature and Role of Various Si-Based Sensitizers for Er ³⁺ Ions in Silicon-Rich Silicon Oxide Thin Films. Advanced Materials Research, 0, 324, 81-84.	0.3	1
442	Analysis of Lattice Distortion in Multicrystalline Silicon for Photovoltaic Cells by Synchrotron White X-Ray Microbeam Diffraction. Materials Science Forum, 0, 725, 153-156.	0.3	1
443	Structural Study of Small Angle Grain Boundaries in Multicrystalline Si. Materials Science Forum, 0, 725, 157-160.	0.3	6
444	Evaluation of Silicon Substrates Fabricated by Seeding Cast Technique. Materials Science Forum, 0, 725, 133-136.	0.3	1
445	Effect of Si ₃ N ₄ Coating on Strain and Fracture of Si Ingots. Materials Science Forum, 0, 725, 247-250.	0.3	2
446	Characterization of Residual Strain in Si Ingots Grown by the Seed-Cast Method. Solid State Phenomena, 0, 205-206, 94-99.	0.3	4
447	Textured Beta-Sialon:Eu ²⁺ Phosphor Deposits Fabricated by Electrophoretic Deposition (EPD) Process within a Strong Magnetic Field: Preparation Process and Photoluminescence (PL) Properties Depending on Orientation. Key Engineering Materials, 0, 654, 268-273.	0.4	0
448	Statistical Consideration of Grain Growth Mechanism of Multicrystalline Si by One-Directional Solidification Technique. Solid State Phenomena, 0, 242, 35-40.	0.3	0
449	50 cm Size Seed Cast Si Ingot Growth and its Characterization. Solid State Phenomena, 0, 242, 30-34.	0.3	2
450	Characterization of Comet-Shaped Defects on C-Face 4H-SiC Epitaxial Wafers. Materials Science Forum, 0, 821-823, 173-176.	0.3	0

#	ARTICLE	IF	CITATIONS
451	Luminescent Characteristics of Undoped and Er-Doped ZnO Thin Films. Key Engineering Materials, 0, , 189-192.	0.4	1